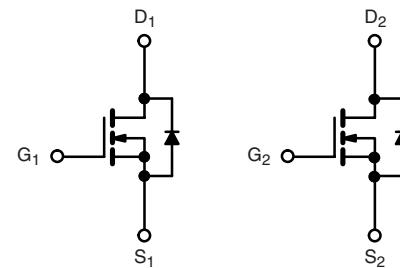
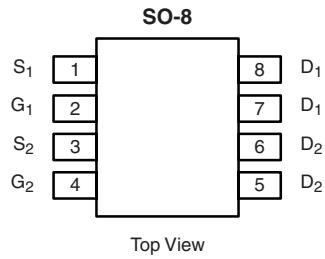


Dual N-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
20	0.019 at $V_{GS} = 4.5$ V	7.1
	0.026 at $V_{GS} = 2.5$ V	6.0

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC



ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	
Continuous Drain Current ($T_J = 150$ °C) ^a	$T_A = 25$ °C	7.1	A
	$T_A = 70$ °C	5.7	
Pulsed Drain Current (10 μ s Pulse Width)	I_{DM}	40	
Continuous Source Current (Diode Conduction) ^a	I_S	1.7	
Maximum Power Dissipation ^a	$T_A = 25$ °C	2	W
	$T_A = 70$ °C	1.3	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	62.5	°C/W

Notes:

a. Surface Mounted on FR4 board, $t \leq 10$ s.

SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted

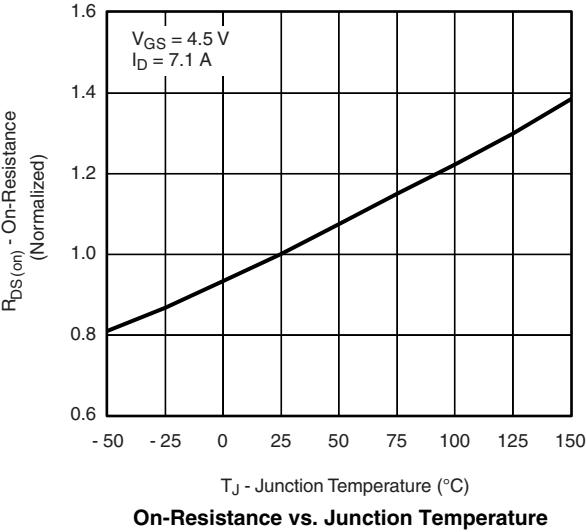
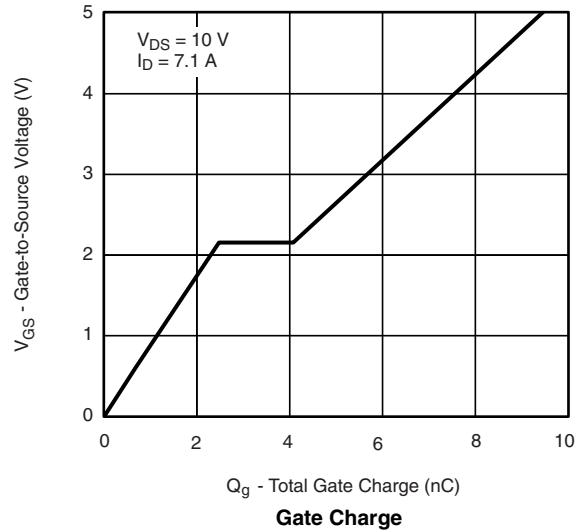
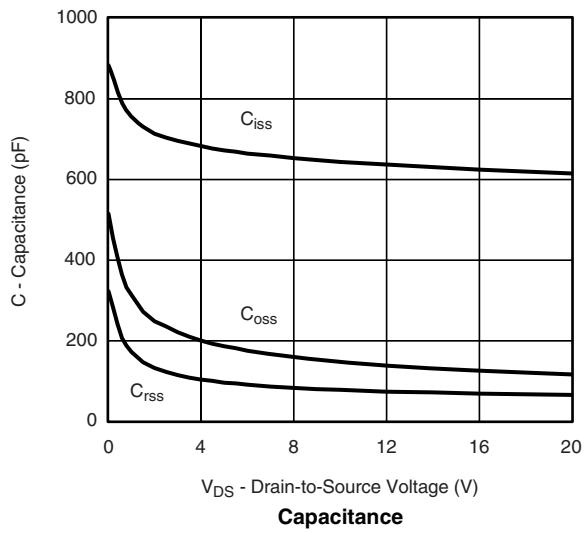
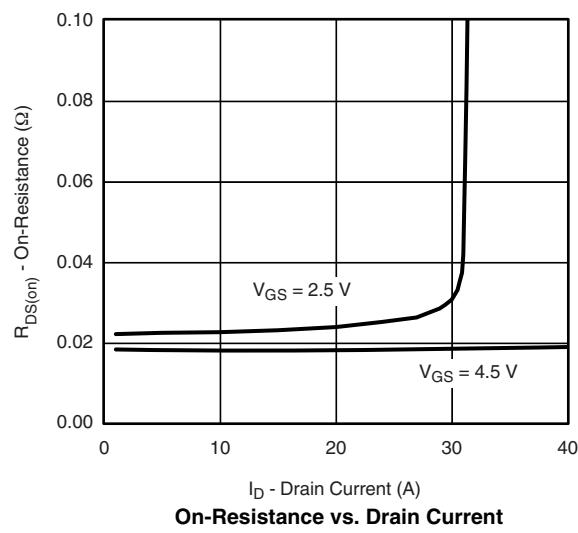
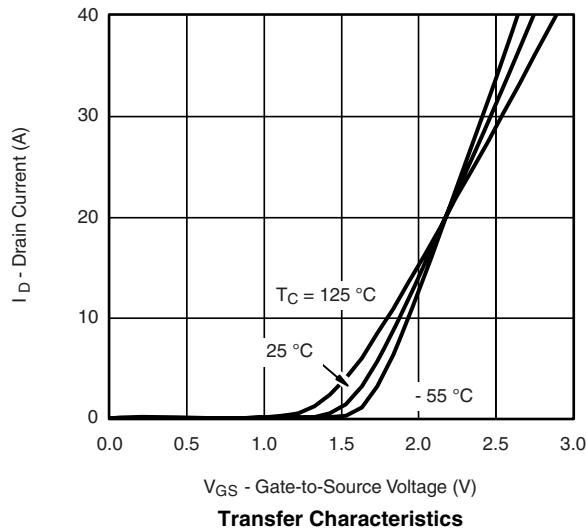
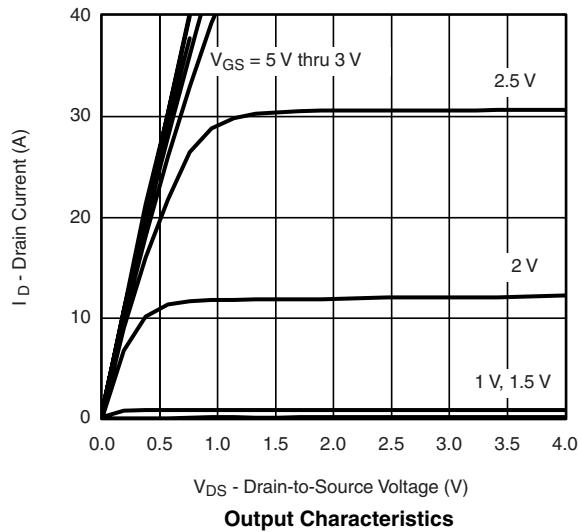
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	0.6		1.5	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}$, $V_{GS} = \pm 12 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20 \text{ V}$, $V_{GS} = 0 \text{ V}$		1	5	μA
		$V_{DS} = 20 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 55^\circ\text{C}$				
On-State Drain Current ^a	$I_{D(\text{on})}$	$V_{DS} \geq 5 \text{ V}$, $V_{GS} = 4.5 \text{ V}$	20			A
Drain-Source On-State Resistance ^a	$R_{DS(\text{on})}$	$V_{GS} = 4.5 \text{ V}$, $I_D = 7.1 \text{ A}$		0.019	0.026	Ω
		$V_{GS} = 2.5 \text{ V}$, $I_D = 6.0 \text{ A}$				
Forward Transconductance ^a	g_{fs}	$V_{DS} = 10 \text{ V}$, $I_D = 7.1 \text{ A}$		27		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 1.7 \text{ A}$, $V_{GS} = 0 \text{ V}$			1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 10 \text{ V}$, $V_{GS} = 4.5 \text{ V}$, $I_D = 7.1 \text{ A}$		9.5		nC
Gate-Source Charge	Q_{gs}			1.5		
Gate-Drain Charge	Q_{gd}			2.5		
Gate Resistance	R_g	$f = 1 \text{ MHz}$		1.6	2.7	Ω
Turn-On Delay Time	$t_{d(\text{on})}$	$V_{DD} = 10 \text{ V}$, $R_L = 10 \Omega$ $I_D \geq 1 \text{ A}$, $V_{GEN} = 4.5 \text{ V}$, $R_g = 10\Omega$		10		ns
Rise Time	t_r			15		
Turn-Off Delay Time	$t_{d(\text{off})}$			38		
Fall Time	t_f			25		
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 1.7 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$		26		

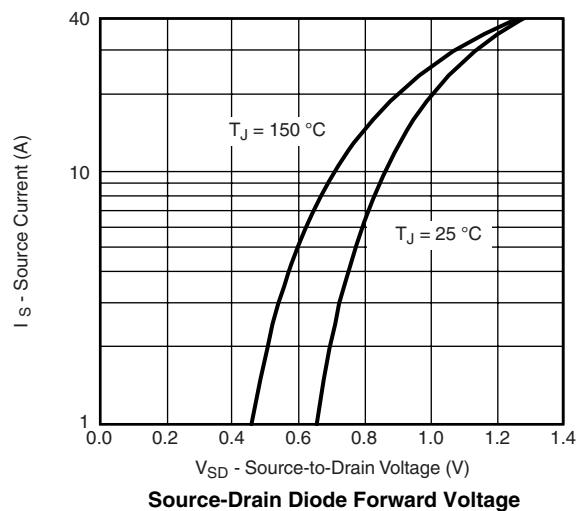
Notes:

a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2 \%$.

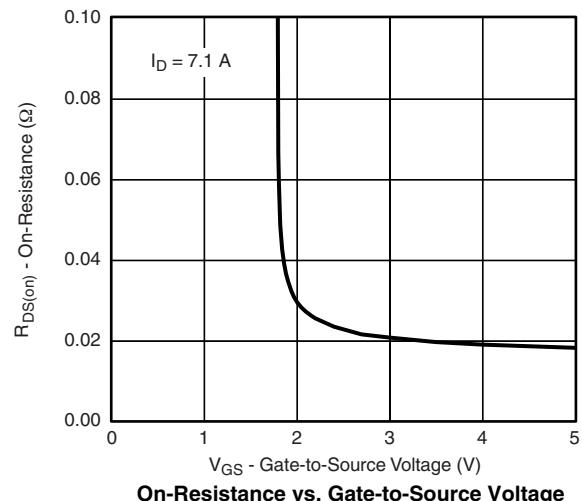
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

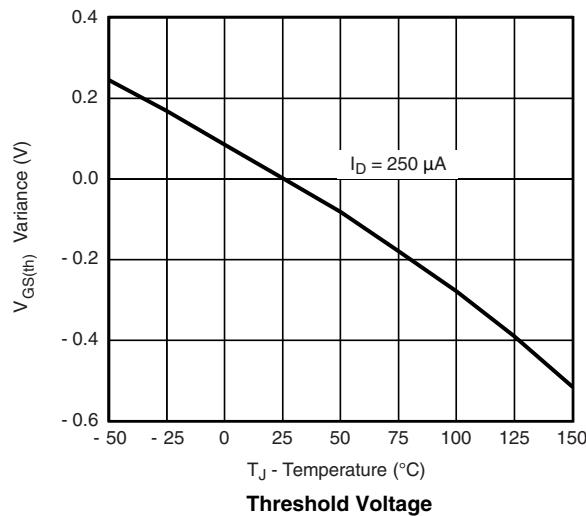
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


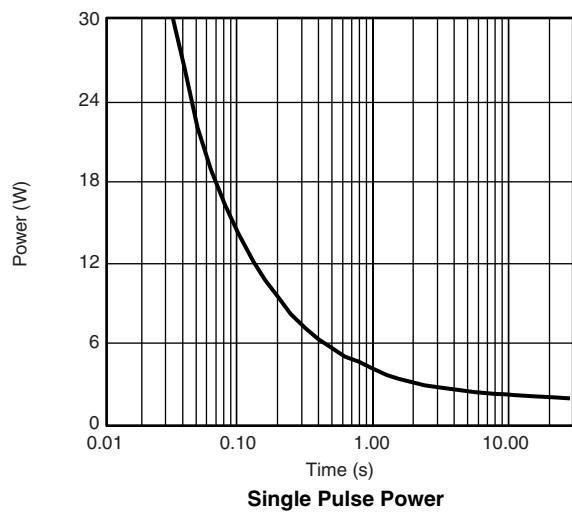
Source-Drain Diode Forward Voltage



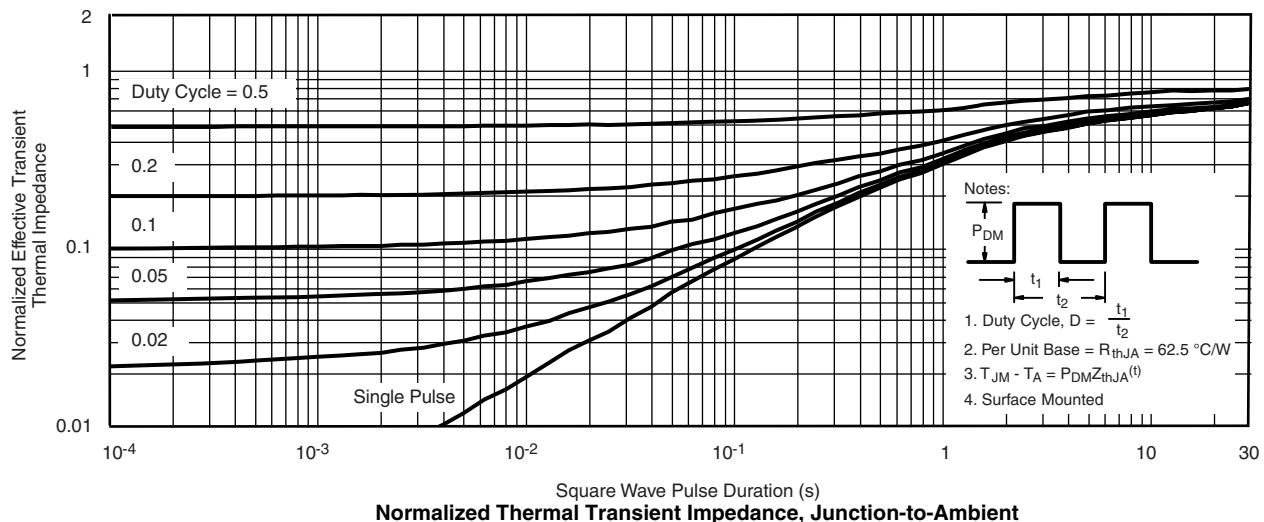
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

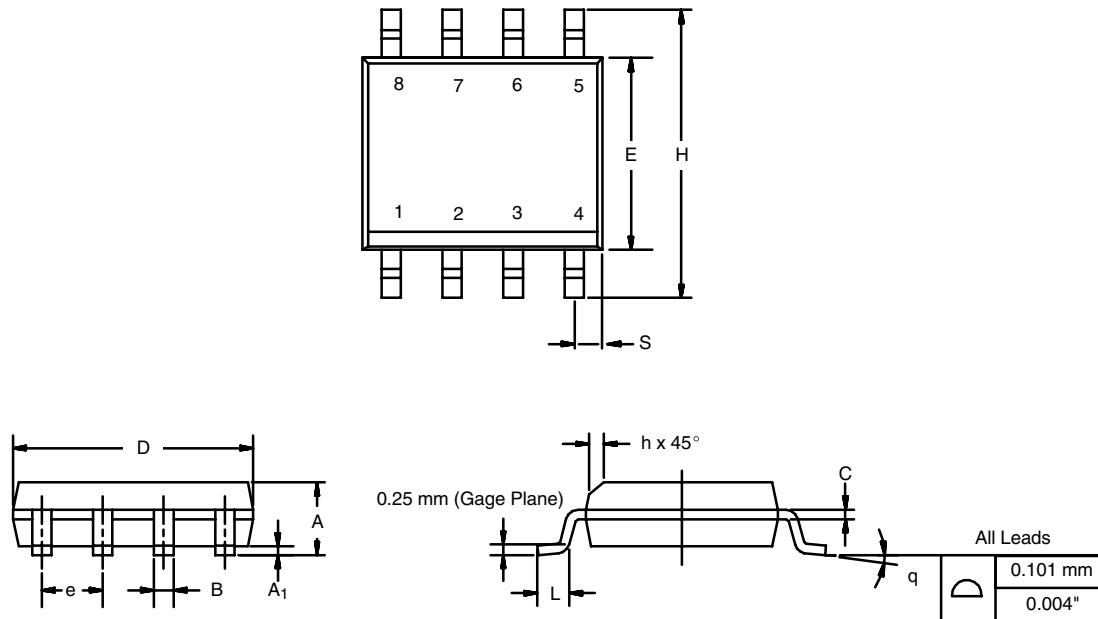


Single Pulse Power



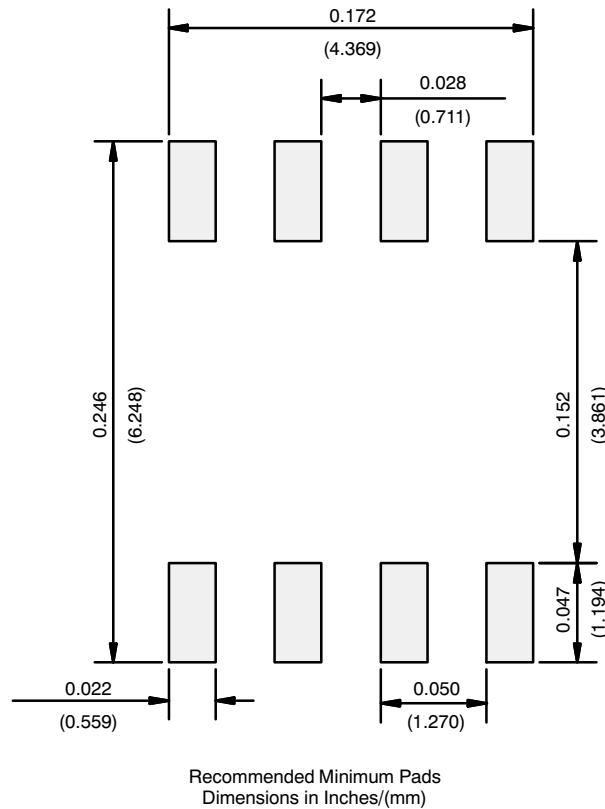
SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



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